



STGW35HF60WD

35 A, 600 V ultra fast IGBT

Features

- Improved E_{off} at elevated temperature
- Minimal tail current
- Low conduction losses
- $V_{CE(sat)}$ classified for easy parallel connection
- Ultra fast soft recovery antiparallel diode

Applications

- Welding
- High frequency converters
- Power factor correction

Description

The STGW35HF60WD is based on a new advanced planar technology concept to yield an IGBT with more stable switching performance (E_{off}) versus temperature, as well as lower conduction losses. The device is tailored to high switching frequency operation (over 100 kHz).

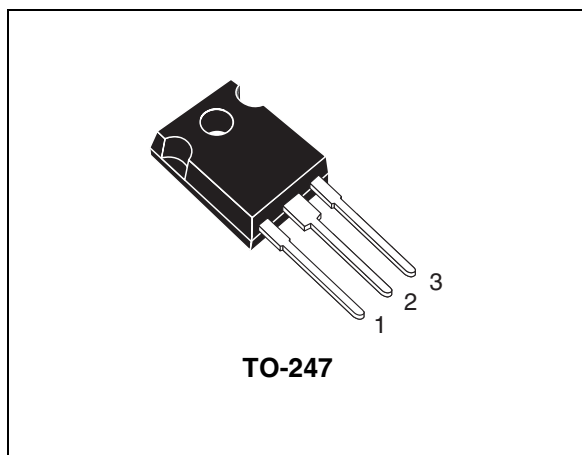


Figure 1. Internal schematic diagram

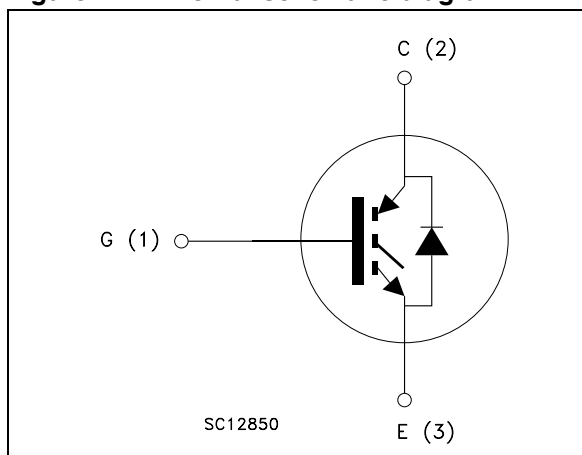


Table 1. Device summary

Order code	Marking ⁽¹⁾	Package	Packaging
STGW35HF60WD	GW35HF60WDA	TO-247	Tube
	GW35HF60WDB		
	GW35HF60WDC		

1. Collector-emitter saturation voltage is classified in group A, B and C, see [Table 5: \$V_{CE\(sat\)}\$ classification](#). STMicroelectronics reserves the right to ship from any group according to production availability.

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)	600	V
$I_C^{(1)}$	Continuous collector current at $T_C = 25\text{ °C}$	60	A
$I_C^{(1)}$	Continuous collector current at $T_C = 100\text{ °C}$	35	A
$I_{CP}^{(2)}$	Pulsed collector current	150	A
$I_{CL}^{(3)}$	Turn-off latching current	80	A
V_{GE}	Gate-emitter voltage	± 20	V
I_F	Diode RMS forward current at $T_C = 25\text{ °C}$	30	A
I_{FSM}	Surge non repetitive forward current $t_p = 10\text{ ms}$ sinusoidal	120	A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	200	W
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Operating junction temperature		

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. Pulse width limited by maximum junction temperature and turn-off within RBSOA

3. $V_{CLAMP} = 80\% (V_{CES})$, $V_{GE} = 15\text{ V}$, $R_G = 10\text{ }\Omega$, $T_J = 150\text{ °C}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case IGBT	0.63	°C/W
	Thermal resistance junction-case diode	1.5	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	50	°C/W

2 Electrical characteristics

($T_J = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 20\text{ A}$			2.5	V
		$V_{GE} = 15\text{ V}, I_C = 20\text{ A}, T_J = 125\text{ °C}$		1.65		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	3.75		5.75	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600\text{ V}$ $V_{CE} = 600\text{ V}, T_J = 125\text{ °C}$			250 1	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			± 100	nA

Table 5. $V_{CE(sat)}$ classification

Symbol	Parameter	Group	Value		Unit
			Min.	Max.	
$V_{CE(sat)}$	Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 20\text{ A}$	A	1.68	1.92	V
		B	1.88	2.17	
		C	2.13	2.50	

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GE} = 0$	-	2400	-	pF
C_{oes}	Output capacitance			235		pF
C_{res}	Reverse transfer capacitance			50		pF
Q_g	Total gate charge	$V_{CE} = 400\text{ V}, I_C = 20\text{ A},$ $V_{GE} = 15\text{ V},$ (see Figure 17)	-	140	-	nC
Q_{ge}	Gate-emitter charge			13		nC
Q_{gc}	Gate-collector charge			52		nC

Table 7. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$		30		ns
t_r	Current rise time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, (see Figure 16)	-	15	-	ns
$(di/dt)_{on}$	Turn-on current slope			1650		A/ μ s
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$		30		ns
t_r	Current rise time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ (see Figure 16)	-	15	-	ns
$(di/dt)_{on}$	Turn-on current slope			1600		A/ μ s
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$, $R_{GE} = 10\ \Omega$, $V_{GE} = 15\text{ V}$	-	30	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 16)		175		ns
t_f	Current fall time			40		ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$, $R_{GE} = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	50	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 16)		225		ns
t_f	Current fall time			70		ns

Table 8. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$		290		μ J
E_{off}	Turn-off switching losses	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, (see Figure 18)	-	185		μ J
E_{ts}	Total switching losses			475		μ J
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$		420		μ J
E_{off}	Turn-off switching losses	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ (see Figure 18)	-	350	530	μ J
E_{ts}	Total switching losses			770		μ J

1. E_{on} is the turn-on losses when a typical diode is used in the test circuit in [Figure 18](#). If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs and diode are at the same temperature (25 °C and 125 °C). E_{on} include diode recovery energy.

Table 9. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	$I_F = 20\text{ A}$ $I_F = 20\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$	-	1.8 1.4	2.25	V V
t_{rr}	Reverse recovery time	$I_F = 20\text{ A}$, $V_R = 50\text{ V}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	50	-	ns
Q_{rr}	Reverse recovery charge	(see Figure 19)		90		nC
I_{rrm}	Reverse recovery current			3		A
t_{rr}	Reverse recovery time	$I_F = 20\text{ A}$, $V_R = 50\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	135	-	ns
Q_{rr}	Reverse recovery charge	(see Figure 19)		375		nC
I_{rrm}	Reverse recovery current			5.5		A

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

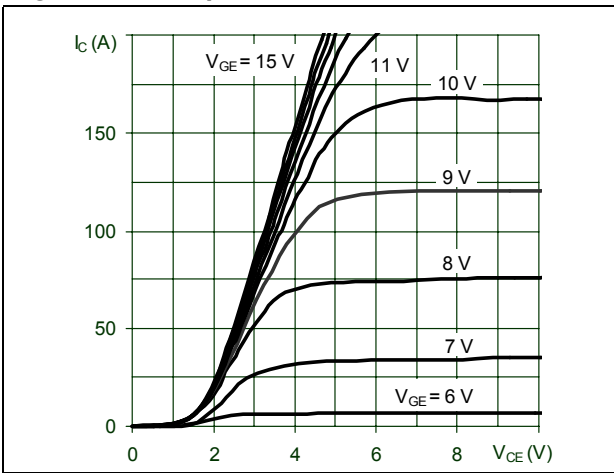


Figure 3. Transfer characteristics

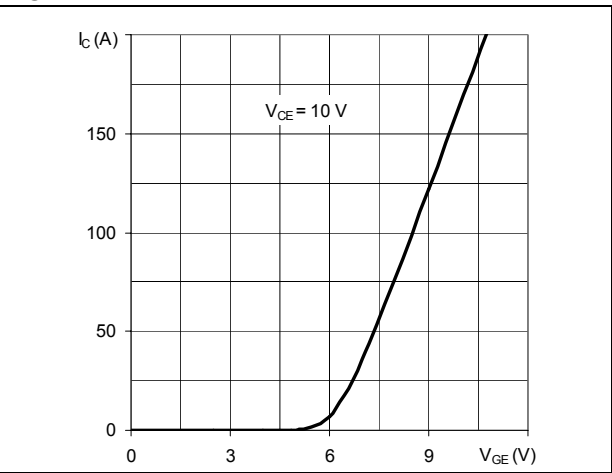


Figure 4. Normalized $V_{CE(sat)}$ vs. I_C

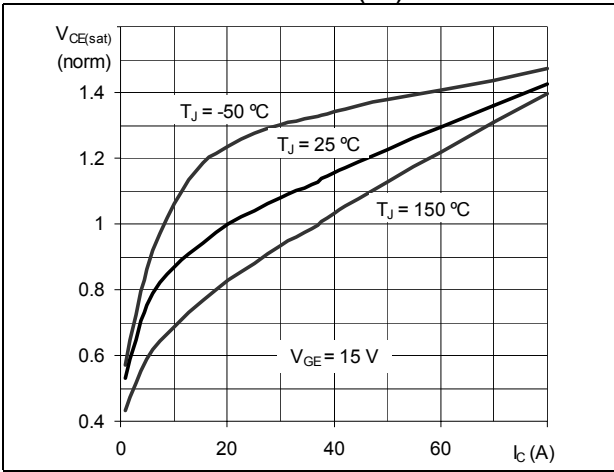


Figure 5. Normalized $V_{CE(sat)}$ vs. temperature

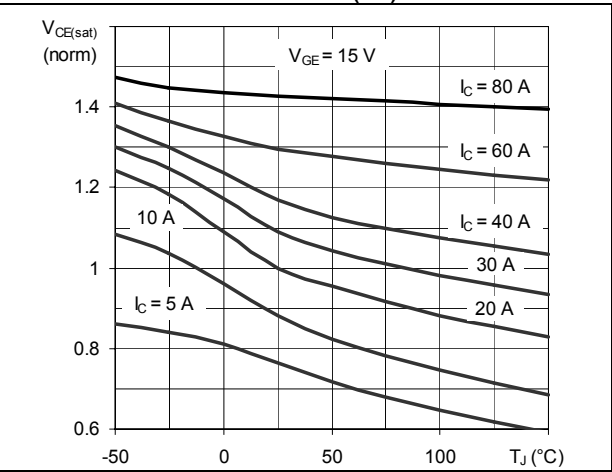


Figure 6. Normalized breakdown voltage vs. temperature

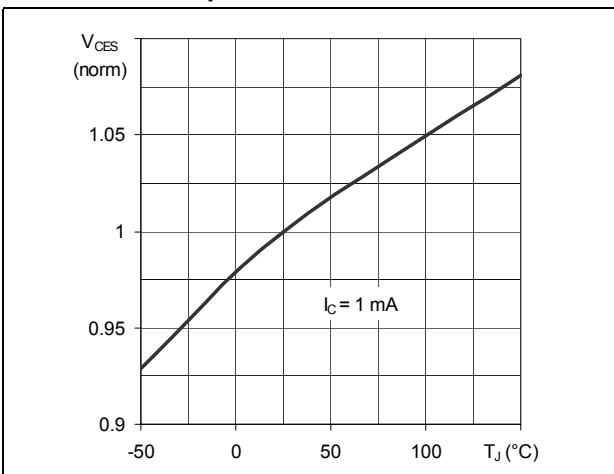


Figure 7. Normalized gate threshold voltage vs. temperature

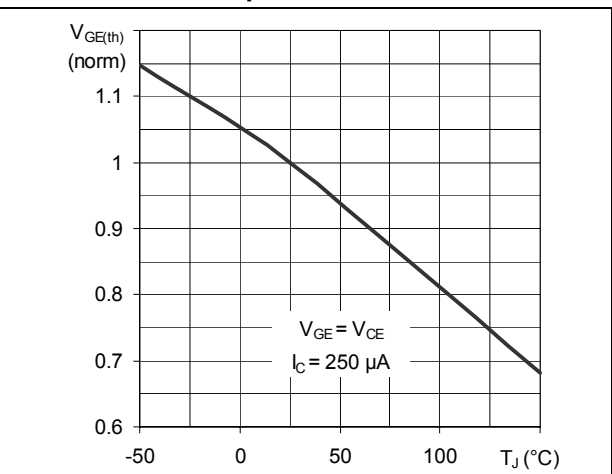


Figure 8. Gate charge vs. gate-emitter voltage

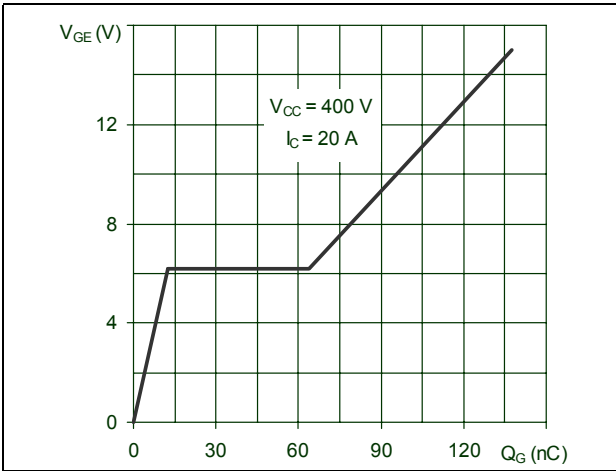


Figure 9. Capacitance variations

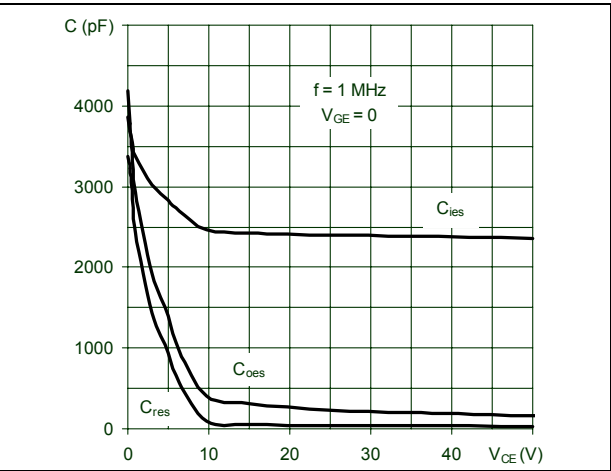


Figure 10. Switching losses vs temperature

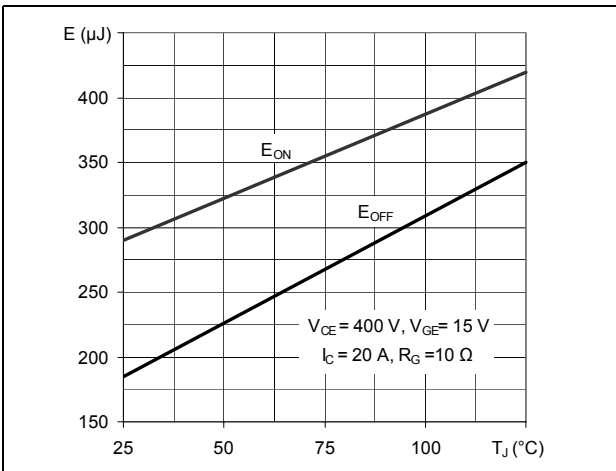


Figure 11. Switching losses vs. gate resistance

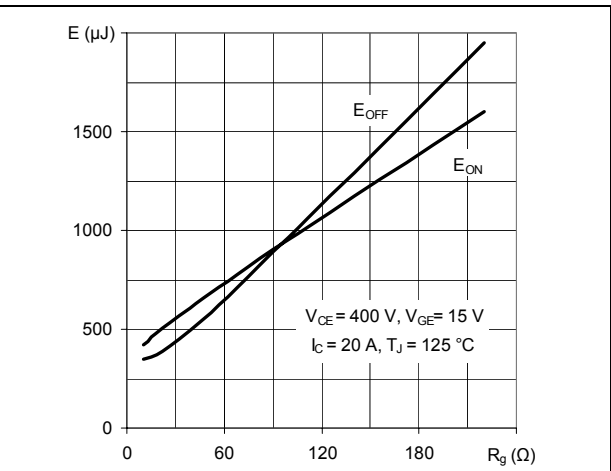


Figure 12. Switching losses vs. collector current

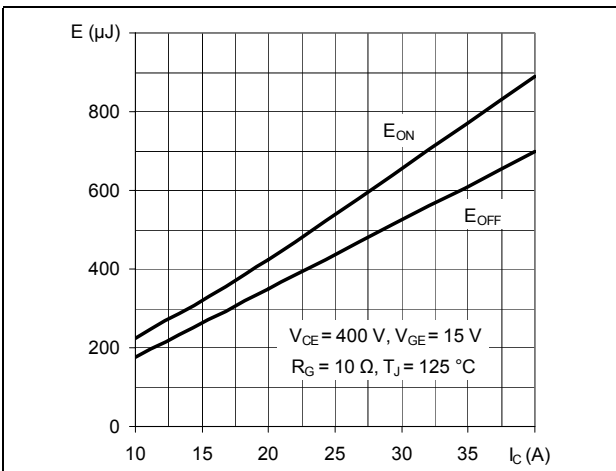


Figure 13. Turn-off SOA

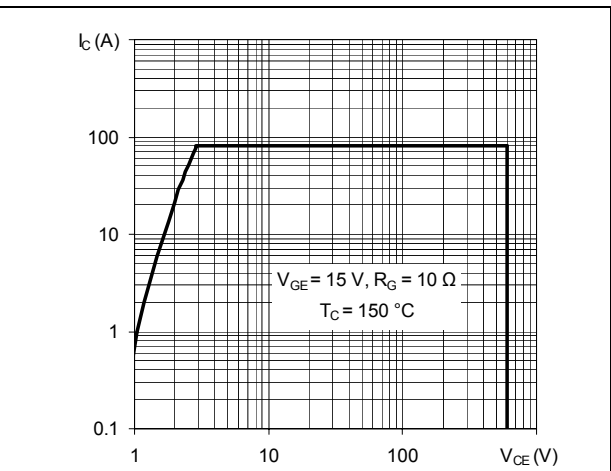


Figure 14. Diode forward on voltage

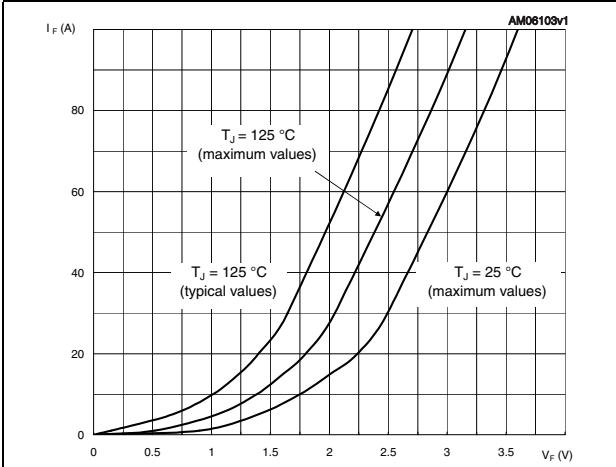
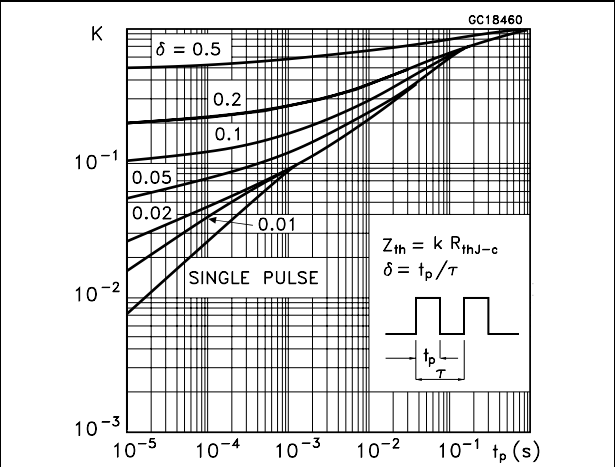


Figure 15. Thermal impedance



3 Test circuits

Figure 16. Test circuit for inductive load switching

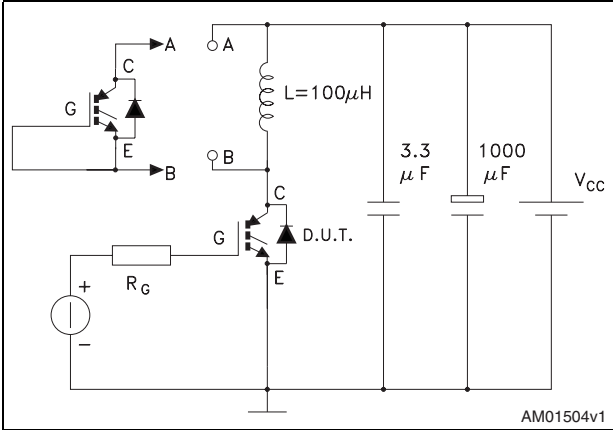


Figure 17. Gate charge test circuit

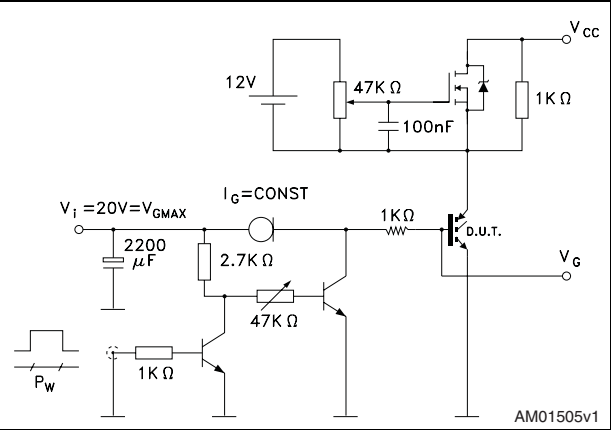


Figure 18. Switching waveform

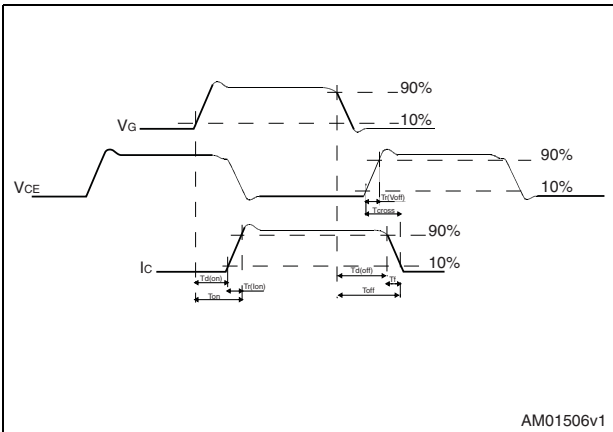
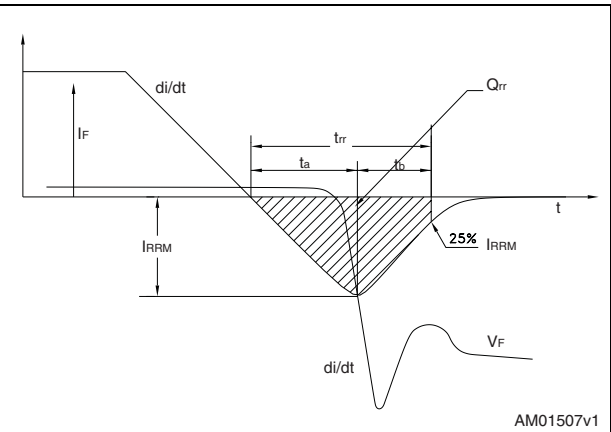


Figure 19. Diode recovery time waveform

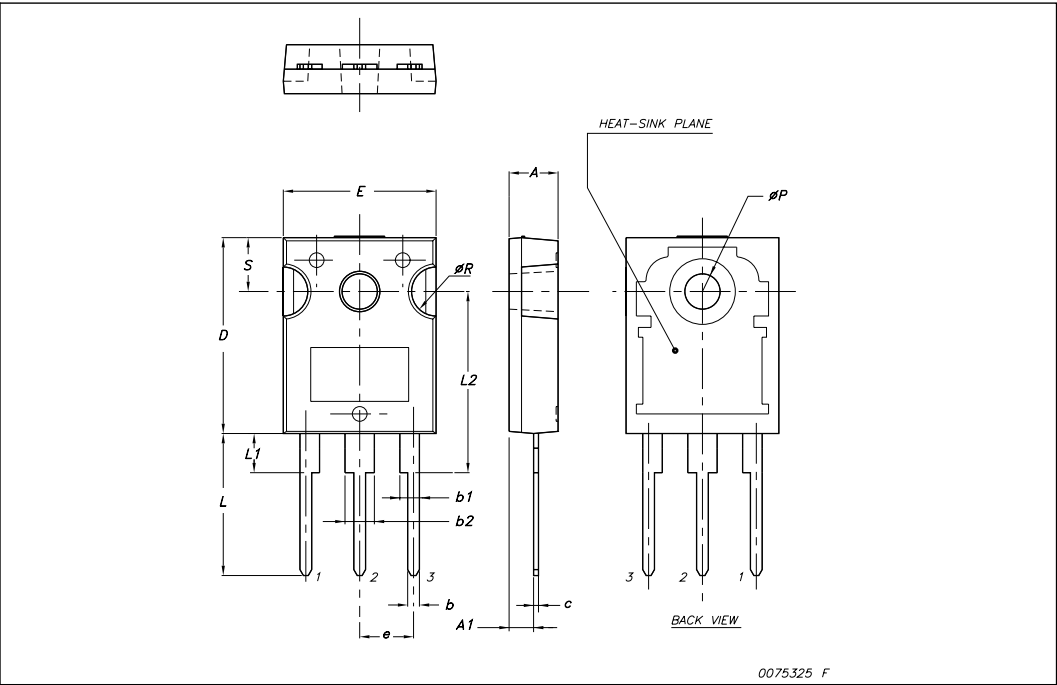


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



5 Revision history

Table 10. Document revision history

Date	Revision	Changes
14-Apr-2009	1	Initial release.
03-Aug-2009	2	Inserted dynamic parameters on Table 6 an Table 7 Document status promoted from preliminary data to datasheet
02-Sep-2009	3	Minor text changes throughout the document Removed watermark
30-Sep-2009	4	Inserted $V_{CE(sat)}$ grouping A, B and C (see Table 5: $V_{CE(sat)}$ classification)
10-May-2010	5	Inserted Section 2.1: Electrical characteristics (curves)

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